

PMEG3015EV

30 V, 1.5 A ultra low V_F MEGA Schottky barrier rectifier in SOT666 package

Rev. 01 — 4 April 2005 Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in an ultra small SMD SOT666 plastic package.

1.2 Features

- Forward current: 1.5 A
- Reverse voltage: 30 V
- Ultra low forward voltage
- Ultra small SMD packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Voltage clamping
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1: Quick reference data

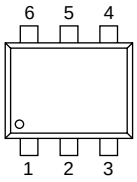
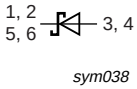
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_F	forward current	$T_{sp} \leq 55$ °C		-	-	1.5	A
V_R	reverse voltage			-	-	30	V
V_F	forward voltage	$I_F = 1.5$ A	[1]	-	480	550	mV

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

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2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	cathode		
2	cathode		
3	anode		
4	anode		
5	cathode		
6	cathode		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PMEG3015EV	-	plastic surface mounted package; 6 leads	SOT666

4. Marking

Table 4: Marking codes

Type number	Marking code
PMEG3015EV	1A

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5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage			-	30	V
I_F	forward current	$T_{sp} \leq 55$ °C		-	1.5	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ ms; $\delta \leq 0.25$	[1]	-	4.5	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8$ ms; square wave	[1]	-	9.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2]	-	0.31	W
			[3]	-	0.58	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–65	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] For SOT666 only valid, if pins 3 and 4 are connected in parallel.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for cathode 1 cm^2.

6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] [2]				
			[3]	-	-	405	K/W
			[4]	-	-	215	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	80	K/W

[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for cathode 1 cm^2.

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7. Characteristics

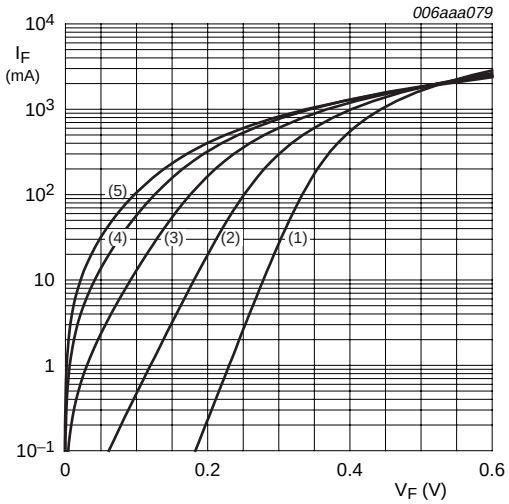
Table 7: Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_F	forward voltage	I_F = 1 mA	[1]	-	125	160	mV
		I_F = 10 mA	[1]	-	185	220	mV
		I_F = 100 mA	[1]	-	255	290	mV
		I_F = 500 mA	[1]	-	340	380	mV
		I_F = 1 A	[1]	-	410	480	mV
		I_F = 1.5 A	[1]	-	480	550	mV
I_R	reverse current	V_R = 10 V		-	60	150	µA
		V_R = 30 V		-	400	1000	µA
C_d	diode capacitance	V_R = 1 V; f = 1 MHz		-	60	72	pF

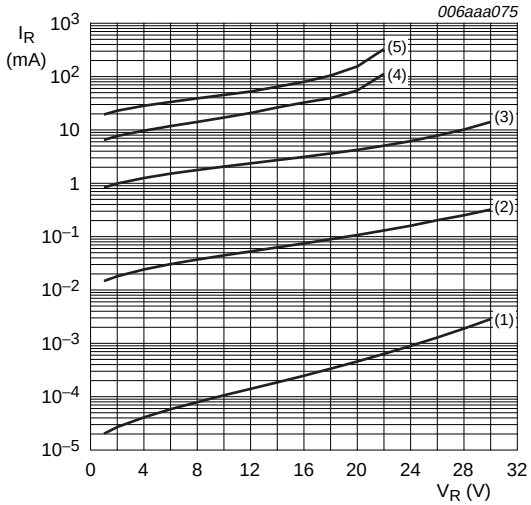
[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

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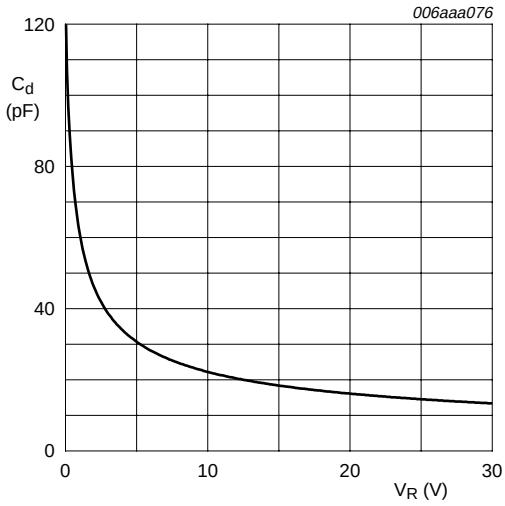
(1) T_{amb} = –40 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 85 °C
(4) T_{amb} = 125 °C
(5) T_{amb} = 150 °C

Fig 1. Forward current as a function of forward voltage; typical values



(1) T_{amb} = –40 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 85 °C
(4) T_{amb} = 125 °C
(5) T_{amb} = 150 °C

Fig 2. Reverse current as a function of reverse voltage; typical values



T_{amb} = 25 °C; f = 1 MHz

Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Package outline

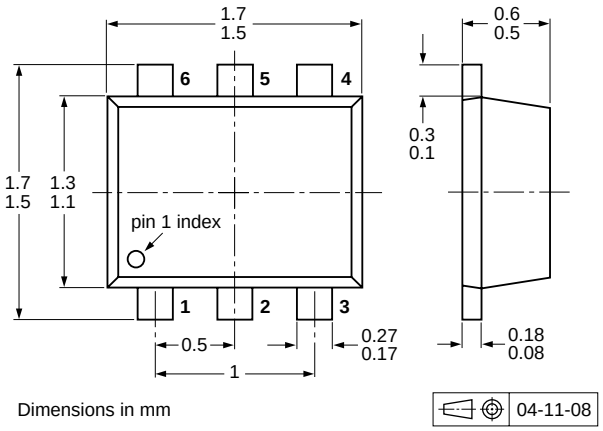


Fig 4. Package outline SOT666

9. Packing information

Table 8: Packing methods

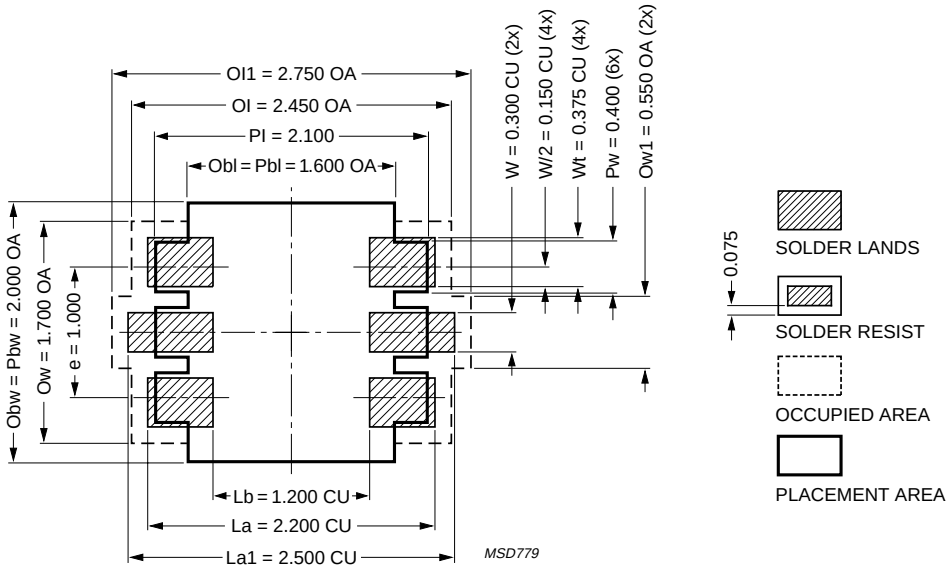
The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity
			4000
PMEG3015EV	SOT666	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see Section 15.

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10. Soldering



Reflow soldering is the only recommended soldering method.

Dimensions in mm

Fig 5. Reflow soldering footprint SOT666

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11. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PMEG3015EV_1	20050404	Product data sheet	-	9397 750 14638	-

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12. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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